

HIGH-FREQUENCY HALF-BRIDGE GATE DRIVER WITH PROGRAMMABLE DEADTIME

Description

The DGD05463 is a high-frequency half-bridge gate driver capable of driving n-channel MOSFETs in a half-bridge configuration. The floating high-side driver is rated up to 50V.

The DGD05463 logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) to interface easily with MCUs. UVLO for high-side and low-side will protect a MOSFET with loss of supply. To protect MOSFETs, cross conduction prevention logic prevents the HO and LO outputs from being on at the same time.

Fast and well-matched propagation delays allow a higher switching frequency, which enable a smaller, more compact power switching design using smaller associated components. The DGD05463 is offered in the W-DFN3030-10 (Type TH) and MSOP-10 packages and operates over an extended -40°C to +125°C temperature range.

Features

- 50V Floating High-Side Driver
- Drives Two N-Channel MOSFETs in a Half-Bridge Configuration
- 1.5A Source / 2.5A Sink Output Current Capability
- Internal Bootstrap Diode Included
- Undervoltage Lockout for High-Side and Low-Side Drivers
- Programmable Deadtime to Protect MOSFETs
- Logic Input (IN and EN) 3.3V Capability
- Ultra-Low Standby Currents (< 1µA)
- Extended Temperature Range: -40°C to +125°C
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](https://www.diodes.com/quality/product-definitions/) or your local Diodes representative.**

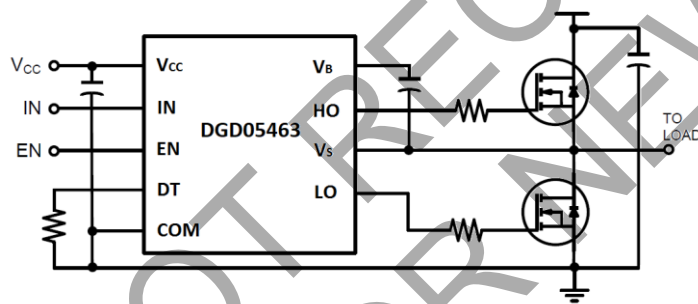
<https://www.diodes.com/quality/product-definitions/>

Applications

- DC-DC converters
- Motor control
- Battery-powered hand tools
- eCig devices
- Class-D power amplifiers

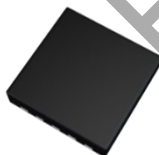
Mechanical Data

- Package: W-DFN3030-10, MSOP-10
- Package Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminals: Finish – Matte Tin Finish. Solderable per MIL-STD-202, Method 208 (E3)
- Weight:
 - W-DFN3030-10 (Type TH): 0.017 grams (Approximate)
 - MSOP-10: 0.0286 grams (Approximate)

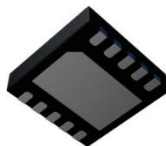


Typical Configuration

W-DFN3030-10 (Type TH)



Top View



Bottom View

MSOP-10



Top View

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Ordering Information (Note 4)

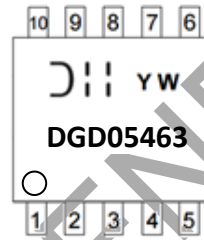
Orderable Part Number	Package	Marking	Reel Size (inches)	Tape Width (mm)	Packing	
					Qty.	Carrier
DGD05463FN-7	W-DFN3030-10 (Type TH)	DGD05463	7	8	3000	Reel
DGD05463M10-13	MSOP-10	DGD05463	13	12	2500	Reel

Note: 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

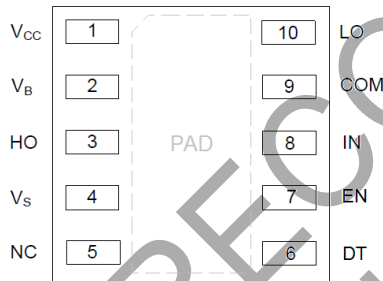


DGD05463 = Product Type Marking Code
YY = Year (ex: 25 = 2025)
WW = Week (01 to 53)

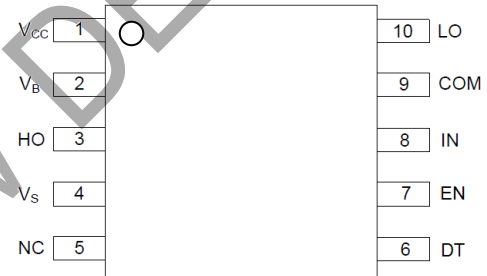


DGD05463 = Product Type Marking Code
Y = Year: 0 to 9 (ex: 5 = 2025)
W = Week: A to Z: week 1 to 26
a to z: week 27 to 52

Pin Diagrams



Top View: W-DFN3030-10 (Type TH)



Top View: MSOP-10

Pin Descriptions

Pin Number	Pin Name	Function
1	V _{CC}	Low-Side and Logic Supply
2	V _B	High-Side Floating Supply
3	HO	High-Side Gate Drive Output
4	V _S	High-Side Floating Supply Return
5	NC	No Connection (No Internal Connection)
6	DT	Deadtime Control
7	EN	Logic Input Enable, a Logic Low Turns Off Gate Driver
8	IN	Logic Input for High-Side and Low-Side Gate Driver Outputs (HO and LO), in Phase with HO
9	COM	Low-Side and Logic Return
10	LO	Low-Side Gate Drive Output
PAD	Substrate	Connect to COM on PCB (For W-DFN3030-10 (Type TH) Only)

The diagram illustrates the internal circuitry of the DGD05463 MOSFET driver. Key components include:

- UV DETECT:** Two UV detection blocks, one for the high-side MOSFET and one for the low-side MOSFET.
- HV LEVEL SHIFT:** A high-voltage level shifter block that interfaces with the high-side MOSFET gate.
- DEAD TIME CONTROL:** A central block that manages the dead time between the high-side and low-side MOSFETs.
- DELAY:** A delay block that provides a controlled delay to the low-side MOSFET gate.
- S-Q Flip-Flops:** Two S-Q flip-flops that generate the drive signals for the high-side and low-side MOSFETs.
- MOSFETs:** Two MOSFETs, one for the high-side (HO) and one for the low-side (LO), connected to the output terminals.
- High Side Well:** A dashed box indicating the high-side well region, which includes the HV LEVEL SHIFT and the top S-Q flip-flop.

The circuit is powered by V_{CC} and includes a V_B output. The input IN is connected to the high-side MOSFET gate. The DT input is connected to the DEAD TIME CONTROL block. The EN input is connected to the low-side MOSFET gate. The output HO is connected to the high-side MOSFET drain. The output LO is connected to the low-side MOSFET drain. The COM terminal is connected to the common ground.

Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
High-Side Floating Positive Supply Voltage	V_B	-0.3 to +60	V
High-Side Floating Negative Supply Voltage	V_S	$V_B - 14$ to $V_B + 0.3$	V
High-Side Floating Output Voltage	V_{HO}	$V_S - 0.3$ to $V_B + 0.3$	V
Offset Supply Voltage Transient	dV_S / dt	50	V/ns
Logic and Low-Side Fixed Supply Voltage	V_{CC}	-0.3 to +14	V
Low-Side Output Voltage	V_{LO}	-0.3 to $V_{CC} + 0.3$	V
Logic Input Voltage (IN and EN)	V_{IN}	-0.3 to $V_{CC} + 0.3$	V

Thermal Characteristics – W-DFN3030-10 (Type TH) (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor (Note 5)	P_D	0.4	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	64	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case (Note 5)	$R_{\theta JC}$	42	$^\circ\text{C/W}$
Operating Temperature	T_J	+150	$^\circ\text{C}$
Lead Temperature (Soldering, 10s)	T_L	+300	
Storage Temperature Range	T_{STG}	-55 to +150	

Note: 5. When mounted on a standard JEDEC 2-layer FR-4 board.

Thermal Characteristics – MSOP-10 (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor (Note 6)	P_D	0.75	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	166	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case (Note 6)	$R_{\theta JC}$	32	$^\circ\text{C/W}$
Operating Temperature	T_J	+150	$^\circ\text{C}$
Lead Temperature (Soldering, 10s)	T_L	+300	
Storage Temperature Range	T_{STG}	-55 to +150	

Note: 6. When mounted on a standard JEDEC 2-layer FR-4 board with minimum recommended pad layout.

Recommended Operating Conditions

Parameter	Symbol	Min	Max	Unit
High-Side Floating Supply	V_B	$V_S + 4.2$	$V_S + 14$	V
High-Side Floating Supply Offset Voltage	V_S	(Note 7)	50 (Note 8)	V
High-Side Floating Output Voltage	V_{HO}	V_S	V_B	V
Logic and Low-Side Fixed Supply Voltage	V_{CC}	4.5 (Note 9)	14	V
Low-Side Output Voltage	V_{LO}	0	V_{CC}	V
Logic Input Voltage (IN and EN)	V_{IN}	0	5	V
Ambient Temperature	T_A	-40	+125	$^\circ\text{C}$

Notes: 7. Logic operation for V_S of -5V to +50V.

8. Provided V_B does not exceed absolute maximum rating of 60V.

9. For operation of $V_{CC} = 4.5\text{V}$ to 4.9V , an external bootstrap Schottky diode ($0.3\text{V } V_{FD}$, 1A) is necessary, as shown in Figure 3. For operation $V_{CC} \geq 4.9\text{V}$, the external Schottky diode is not required.

DC Electrical Characteristics ($V_{CC} = V_{BS} = 12V$, $COM = V_S = 0$, @ $T_A = +25^\circ C$, unless otherwise specified.) (Note 10)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Logic "1" Input Voltage	V_{IH}	2.4	—	—	V	—
Logic "0" Input Voltage	V_{IL}	—	—	0.8	V	—
Enable Logic "1" Input Voltage	V_{ENIH}	1.5	—	—	V	—
Enable Logic "0" Input Voltage	V_{ENIL}	—	—	0.7	V	—
Input Voltage Hysteresis	V_{INHYS}	—	0.6	—	V	—
High-Level Output Voltage, $V_{BIAS} - V_O$	V_{OH}	—	0.45	0.6	V	$I_{O+} = 100mA$
Low-Level Output Voltage, V_O	V_{OL}	—	0.15	0.22	V	$I_{O-} = 100mA$
Offset Supply Leakage Current	I_{LK}	—	10	50	μA	$V_B = V_S = 60V$
V_{CC} Shutdown Supply Current	I_{CCSD}	—	0	1	μA	$V_{IN} = 0$ or $5V$, $V_{EN} = 0$
V_{CC} Quiescent Supply Current	I_{CCQ}	—	0.28	0.5	mA	$V_{IN} = 0$ or $5V$ $R_{DT} = 100k\Omega$
V_{CC} Operating Supply Current	I_{CCOP}	—	7.6	—	mA	$f_s = 500kHz$, $C_L = 1000pF$
V_{BS} Quiescent Supply Current	I_{BSQ}	—	32	100	μA	$V_{IN} = 0$ or $5V$
V_{BS} Operating Supply Current	I_{BSOP}	—	7.6	—	mA	$f_s = 500kHz$, $C_L = 1000pF$
Logic "1" Input Bias Current	I_{IN+}	—	25	60	μA	$V_{IN} = 5V$
Logic "0" Input Bias Current	I_{IN-}	—	0	1	μA	$V_{IN} = 0$
V_{BS} Supply Undervoltage Positive Going Threshold	V_{BSUV+}	3.3	3.8	4.4	V	—
V_{BS} Supply Undervoltage Negative Going Threshold	V_{BSUV-}	2.9	3.3	3.9	V	—
V_{CC} Supply Undervoltage Positive Going Threshold	V_{CCUV+}	3.3	3.8	4.4	V	—
V_{CC} Supply Undervoltage Negative Going Threshold	V_{CCUV-}	2.9	3.3	3.9	V	—
Output High Short-Circuit Pulsed Current	I_{O+}	1.0	1.5	—	A	$V_O = 0$, $P_W \leq 10\mu s$
Output Low Short-Circuit Pulsed Current	I_{O-}	1.9	2.5	—	A	$V_O = 15V$, $P_W \leq 10\mu s$
Forward Voltage of Bootstrap Diode	V_{F1}	—	0.67	—	V	$I_F = 100\mu A$
Forward Voltage of Bootstrap Diode	V_{F2}	—	1.7	—	V	$I_F = 100mA$

Note: 10. The V_{IN} and I_{IN} parameters are applicable to the two logic pins: IN and EN. The V_O and I_O parameters are applicable to the respective output pins: HO and LO.

AC Electrical Characteristics ($V_{CC} = V_{BS} = 12V$, $COM = V_S = 0$, $C_L = 1000pF$, @ $T_A = +25^\circ C$, unless otherwise specified.)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Turn-on Propagation Delay, HO & LO	t_{on}	65	96	125	ns	$R_{DT} = 10k\Omega$
		350	463	580	ns	$R_{DT} = 100k\Omega$
Turn-off Propagation Delay, HO & LO	t_{off}	—	22	56	ns	—
Turn-on Rise Time	t_r	—	17	35	ns	—
Turn-off Fall Time	t_f	—	12	25	ns	—
Delay Matching	t_{DM}	—	—	50	ns	—
Deadtime: $t_{DT LO-HO}$ & $t_{DT HO-LO}$	t_{DT}	40	70	100	ns	$R_{DT} = 10k\Omega$
		300	430	560	ns	$R_{DT} = 100k\Omega$
Deadtime Matching	t_{MDT}	—	—	50	ns	$R_{DT} = 100k\Omega$

Timing Waveforms

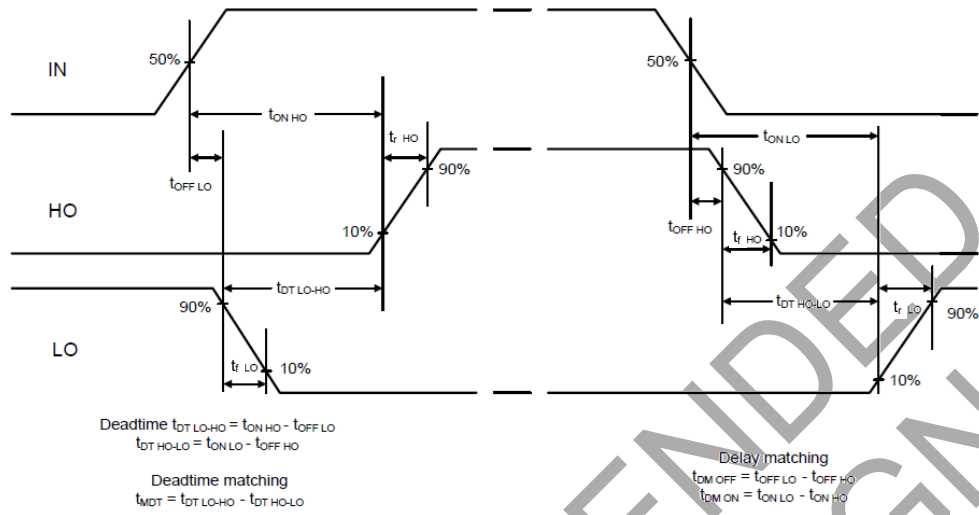


Figure 1. Switching Time Waveform Definitions

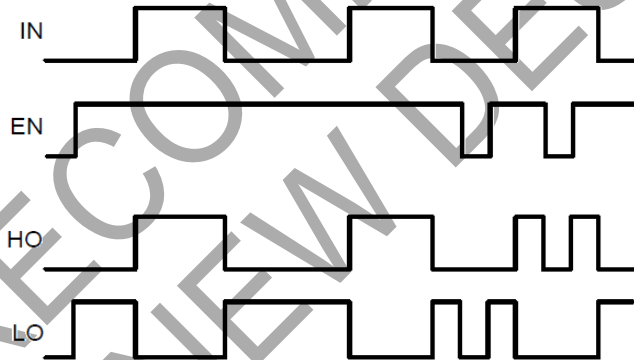


Figure 2. Input / Output Timing Diagram

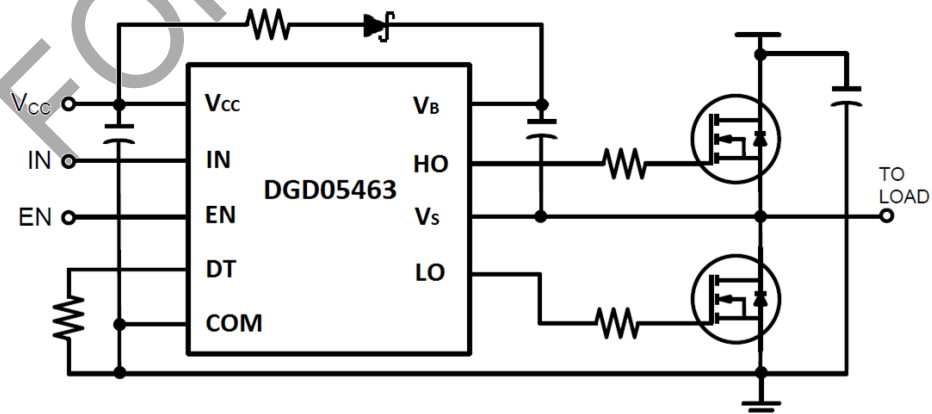


Figure 3. Typical application necessary for $V_{CC} = 4.5V$ to $4.9V$ operation. For $V_{CC} \geq 4.9V$, the bootstrap Schottky diode (0.3V Voltage drop, 1A) and resistor are not required.

Typical Performance Characteristics ($V_{CC} = 12V$, @ $T_A = +25^\circ C$, unless otherwise specified.)

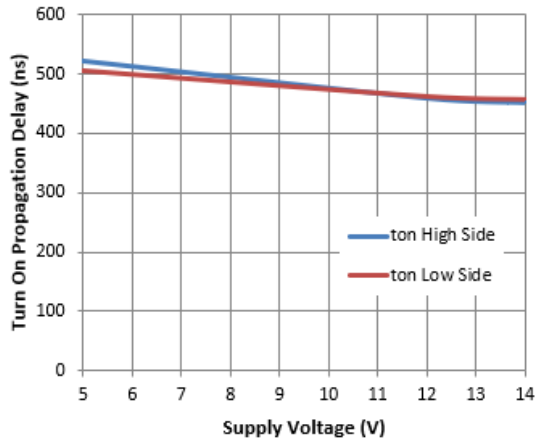


Figure 4. Turn-on Propagation Delay vs. Supply Voltage

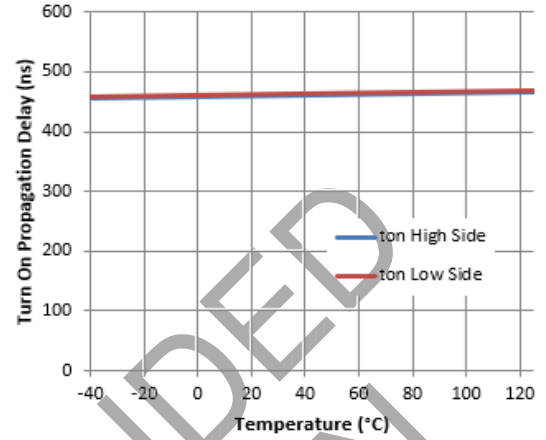


Figure 5. Turn-on Propagation Delay vs. Temperature

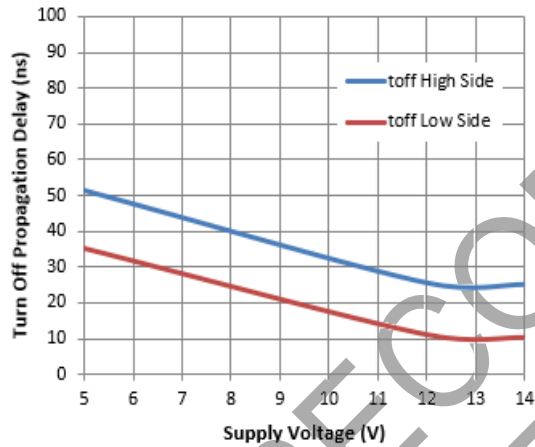


Figure 6. Turn-off Propagation Delay vs. Supply Voltage

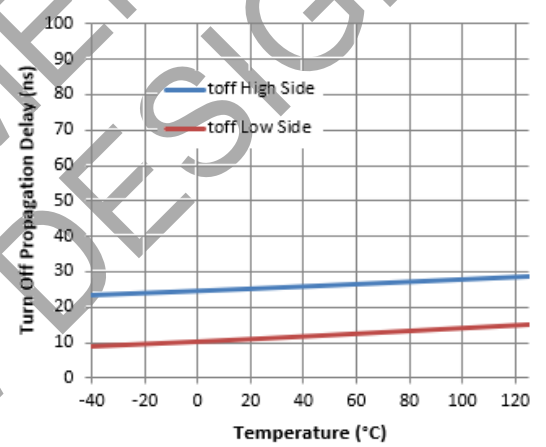


Figure 7. Turn-off Propagation Delay vs. Temperature

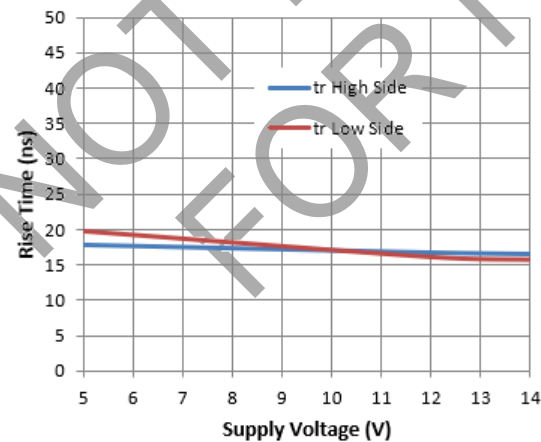


Figure 8. Rise Time vs. Supply Voltage

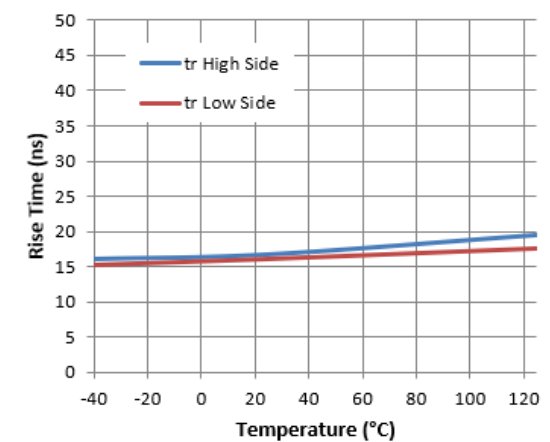


Figure 9. Rise Time vs. Temperature

Typical Performance Characteristics ($V_{CC} = 12V$, @ $T_A = +25^\circ C$, unless otherwise specified.) (continued)

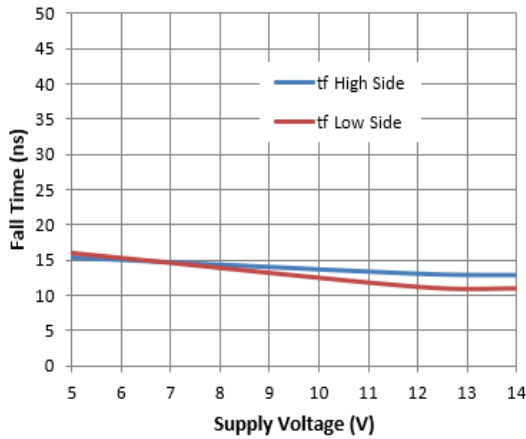


Figure 10. Fall Time vs. Supply Voltage

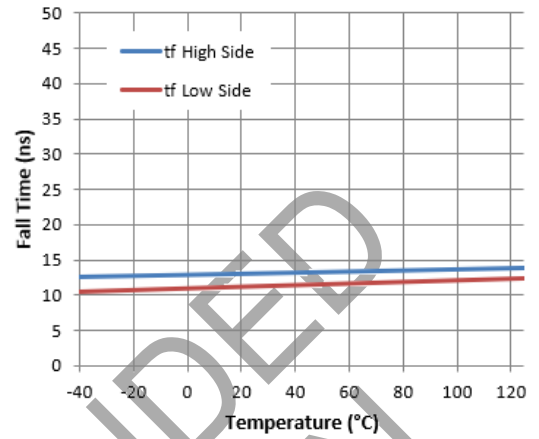


Figure 11. Fall Time vs. Temperature

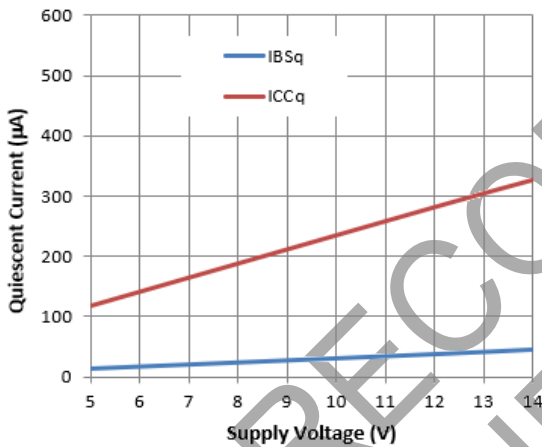


Figure 12. Quiescent Current vs. Supply Voltage

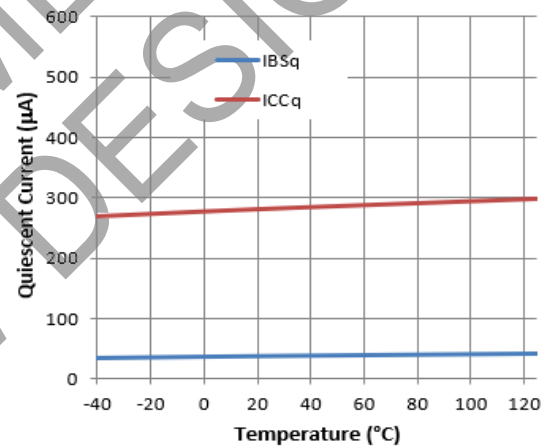


Figure 13. Quiescent Current vs. Temperature

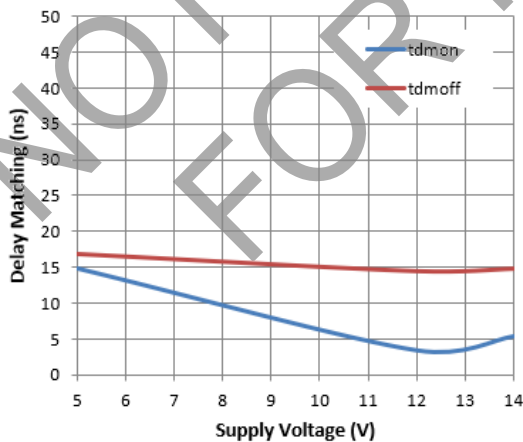


Figure 14. Delay Matching vs. Supply Voltage

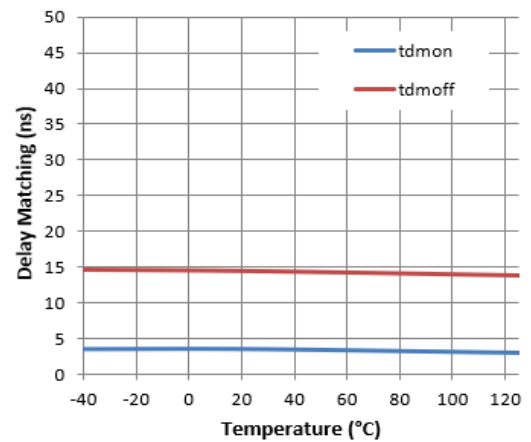


Figure 15. Delay Matching vs. Temperature

Typical Performance Characteristics ($V_{CC} = 12V$, @ $T_A = +25^\circ C$, unless otherwise specified.) (continued)

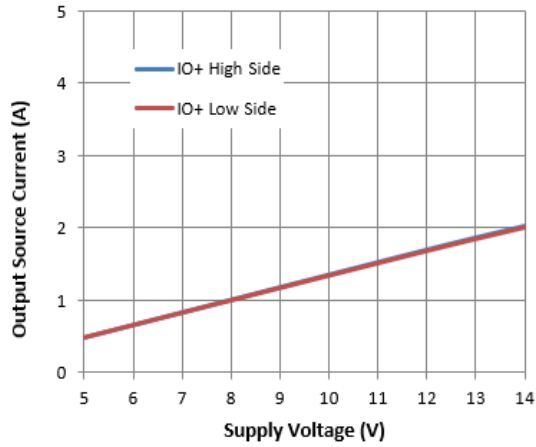


Figure 16. Output Source Current vs. Supply Voltage

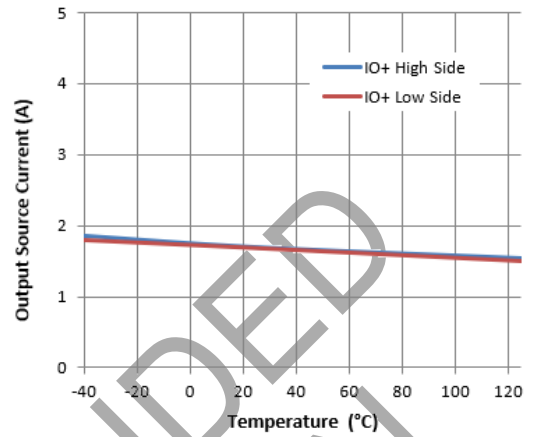


Figure 17. Output Source Current vs. Temperature

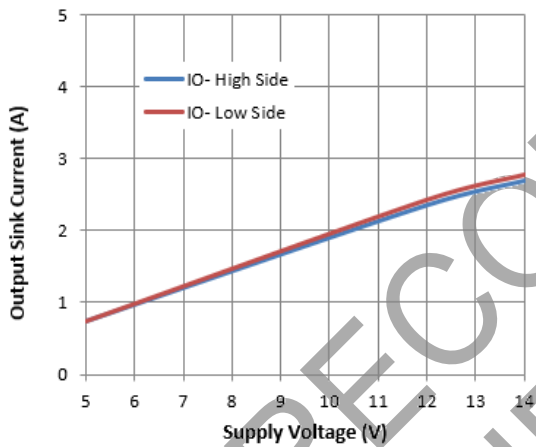


Figure 18. Output Sink Current vs. Supply Voltage

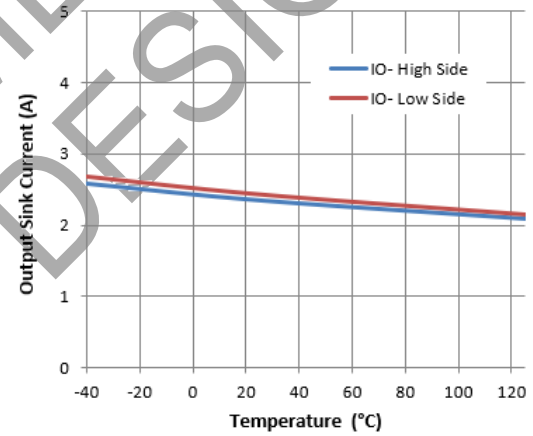


Figure 19. Output Sink Current vs. Temperature

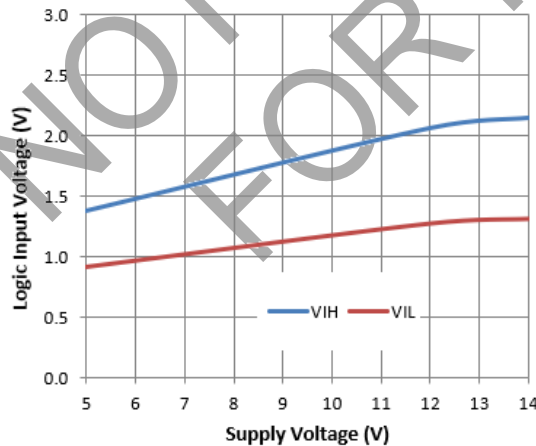


Figure 20. Logic Input Voltage vs. Supply Voltage

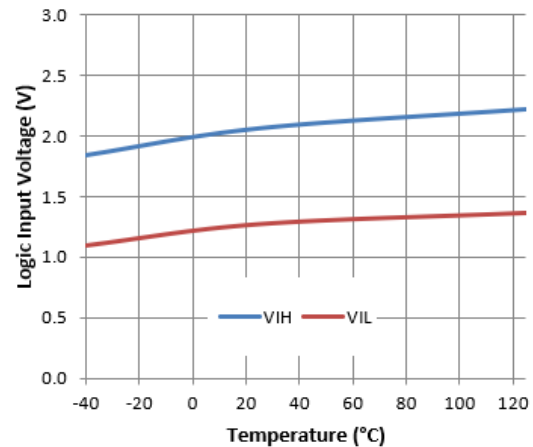


Figure 21. Logic Input Voltage vs. Temperature

Typical Performance Characteristics ($V_{CC} = 12V$, @ $T_A = +25^\circ C$, unless otherwise specified.) (continued)

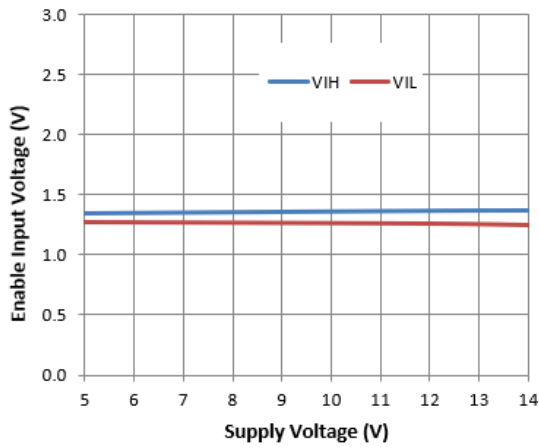


Figure 22. Enable Input Voltage vs. Supply Voltage

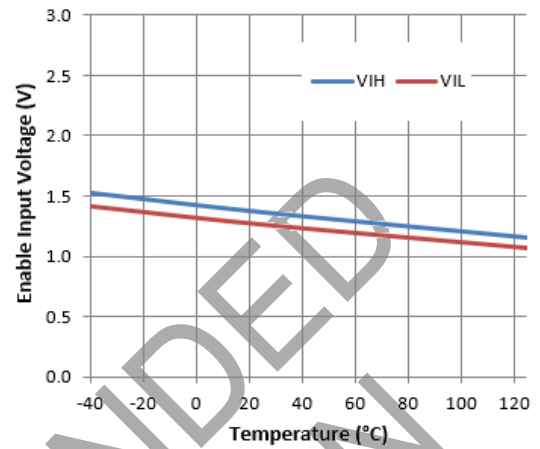


Figure 23. Enable Input Voltage vs. Temperature

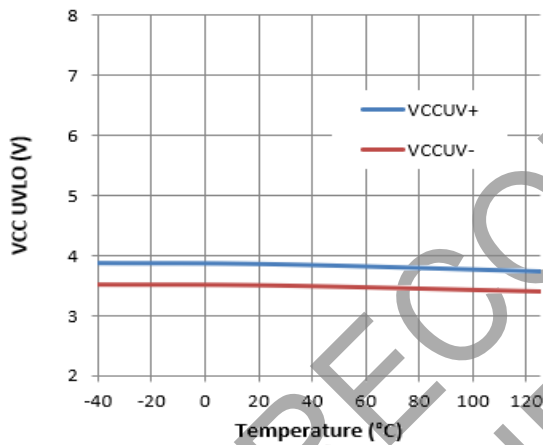


Figure 24. VCC UVLO vs. Temperature

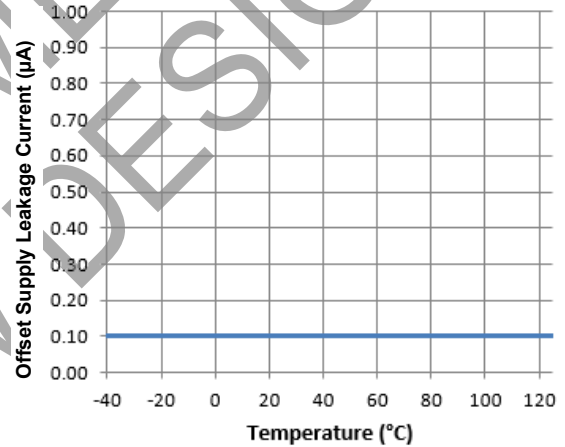


Figure 25. Offset Supply Leakage Current vs. Temperature

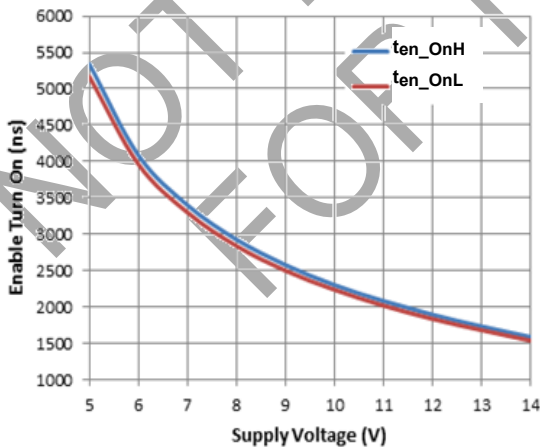


Figure 26. EN to Output t_{on} vs. Supply Voltage

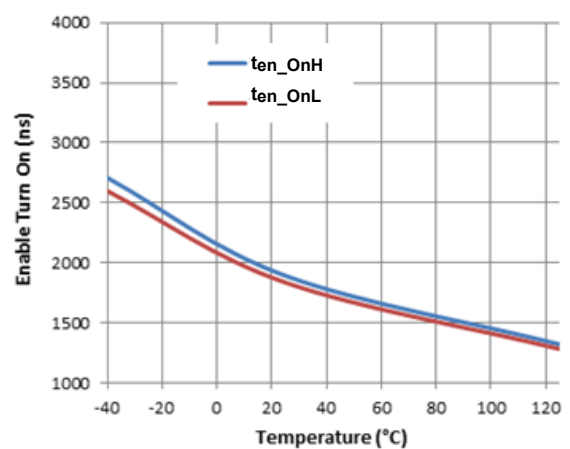


Figure 27. EN to Output t_{on} vs. Temperature

Typical Performance Characteristics ($V_{CC} = 12V$, @ $T_A = +25^\circ C$, unless otherwise specified.) (continued)

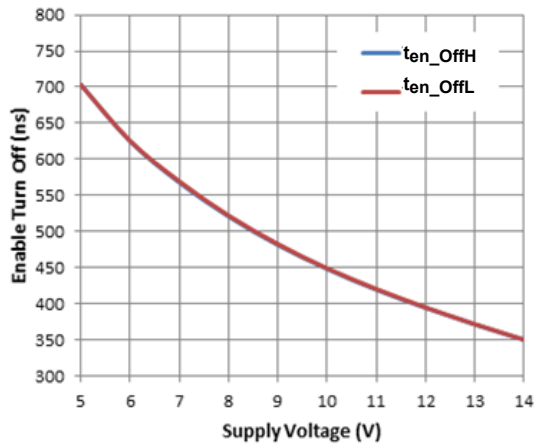


Figure 28. EN to Output t_{off} vs. Supply Voltage

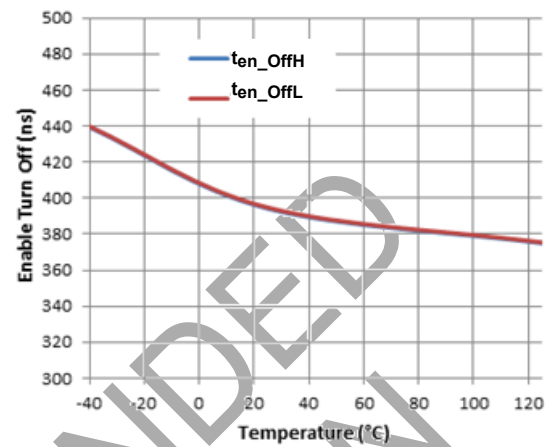
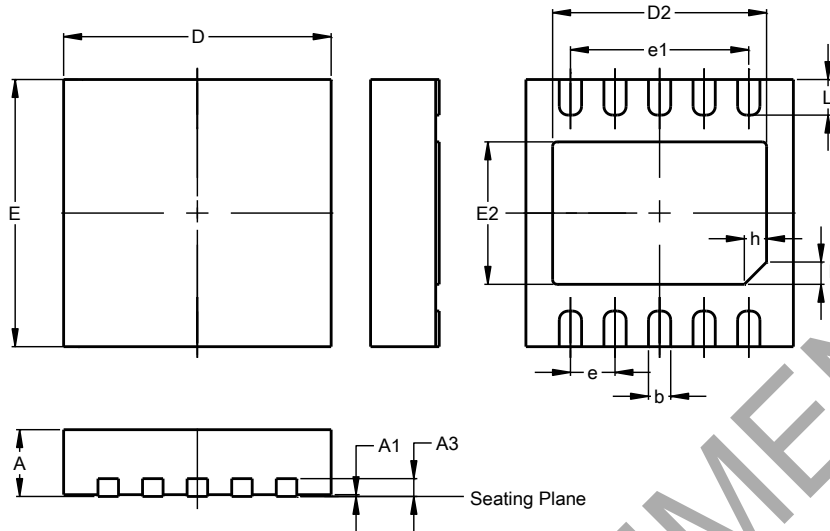


Figure 29. EN to Output t_{off} vs. Temperature

Package Outline Dimensions

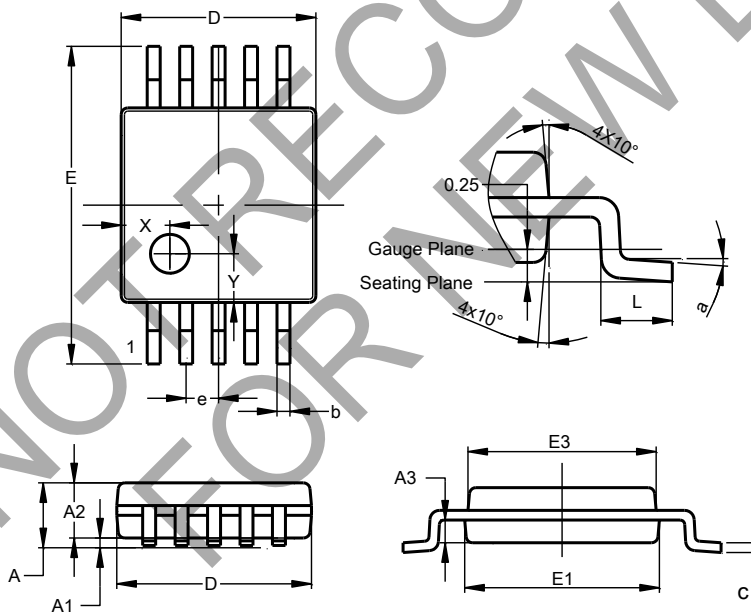
Please see <http://www.diodes.com/package-outlines.html> for the latest version.

W-DFN3030-10 (Type TH)



W-DFN3030-10 (Type TH)			
Dim	Min	Max	Typ
A	0.70	0.80	0.75
A1	--	0.05	0.02
A3	0.18	0.25	0.20
b	0.18	0.30	0.25
D	2.90	3.10	3.00
D2	2.40	2.60	2.50
e	0.50BSC		
e1	2.00BSC		
E	2.90	3.10	3.00
E2	1.45	1.65	1.55
h	0.20	0.30	0.25
L	0.30	0.50	0.40
All Dimensions in mm			

MSOP-10

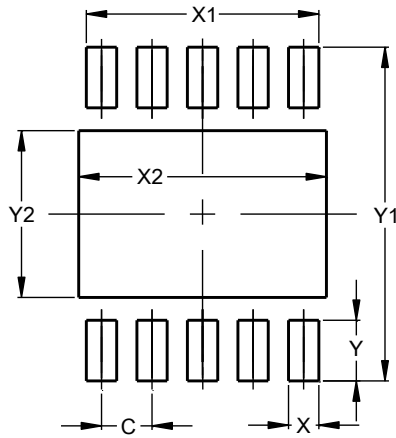


MSOP-10			
Dim	Min	Max	Typ
A	-	1.10	-
A1	0.05	0.15	0.10
A2	0.75	0.95	0.86
A3	0.29	0.49	0.39
b	0.17	0.27	0.20
c	0.08	0.23	0.15
D	2.95	3.05	3.00
e	-	-	0.50
E	4.80	5.00	4.90
E1	2.95	3.05	3.00
E3	2.85	3.05	2.95
L	0.40	0.80	0.60
X	--	--	0.750
Y	--	--	0.750
a	0°	8°	4°
All Dimensions in mm			

Suggested Pad Layout

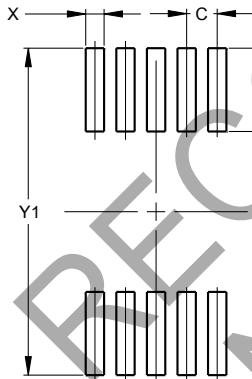
Please see <http://www.diodes.com/package-outlines.html> for the latest version.

W-DFN3030-10 (Type TH)



Dimensions	Value (in mm)
C	0.500
X	0.300
X1	2.300
X2	2.600
Y	0.600
Y1	3.300
Y2	1.650

MSOP-10



Dimensions	Value (in mm)
C	0.50
X	0.30
Y	1.35
Y1	5.30

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